

Supplementary Information

Supersaturation-controlled synthesis of diverse In_2O_3 morphologies and their shapes-dependent sensing performances†

Wei Yang,^{a,b} Peng Wan,^c Hu Meng,^a Jiming Hu,^b and Liang Feng^{*a}

^a Key Lab of Separation Science for Analytical Chemistry, Dalian Institute of Chemical Physics, Chinese Academy of Sciences, Dalian, 116023, China. Email: fengl@dicp.ac.cn; Fax: +86-411-84379411; Tel: +86-411-84379660

^b Key Lab of Analytical Chemistry for Biology and Medicine (Ministry of Education), College of Chemistry and Molecular Sciences, Wuhan University, Wuhan, 430072, China

^c Faculty of Chemical, Environmental and Biological Science and Technology, Dalian University of Technology, Dalian 116024, China

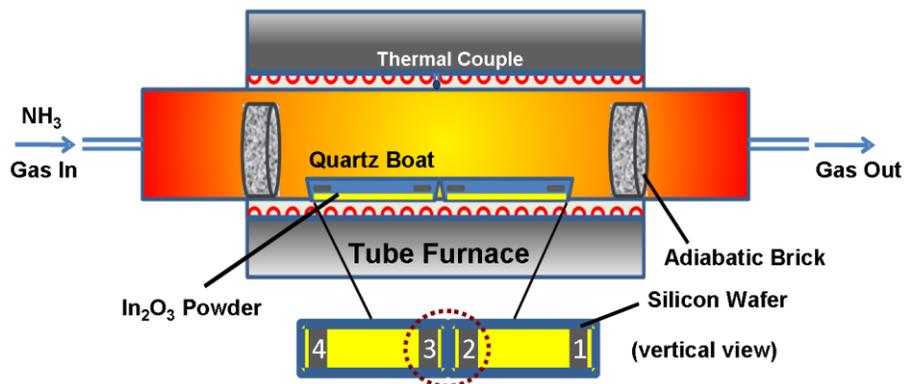


Fig. S1 Schematic illustration of the apparatus used for the synthesis of diverse In₂O₃ morphologies by nitriding In₂O₃ under NH₃ flow at 700 °C for 2 h and subsequently re-oxidized for another 1 h at the same temperature.

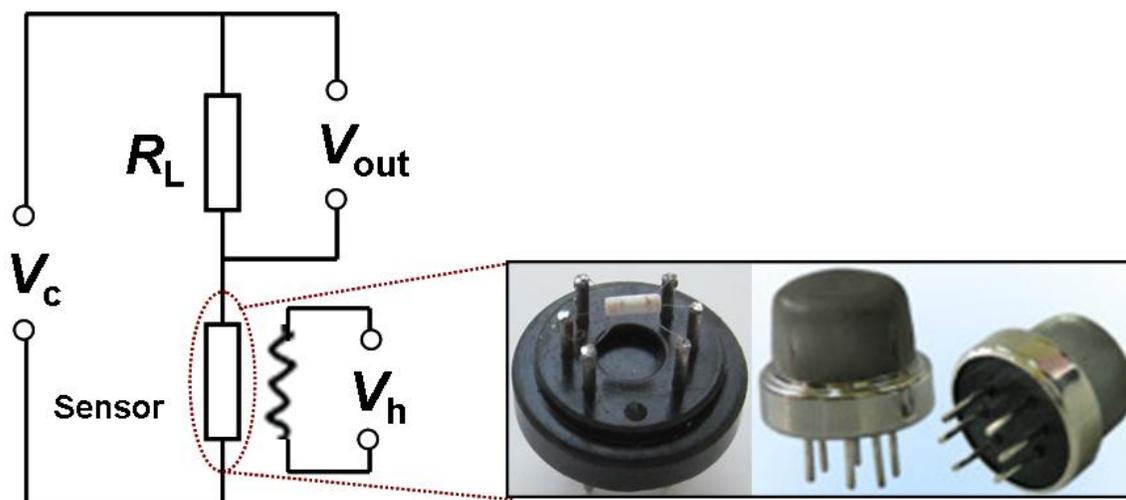


Fig.S2 The measuring electric circuit for the gas sensor.

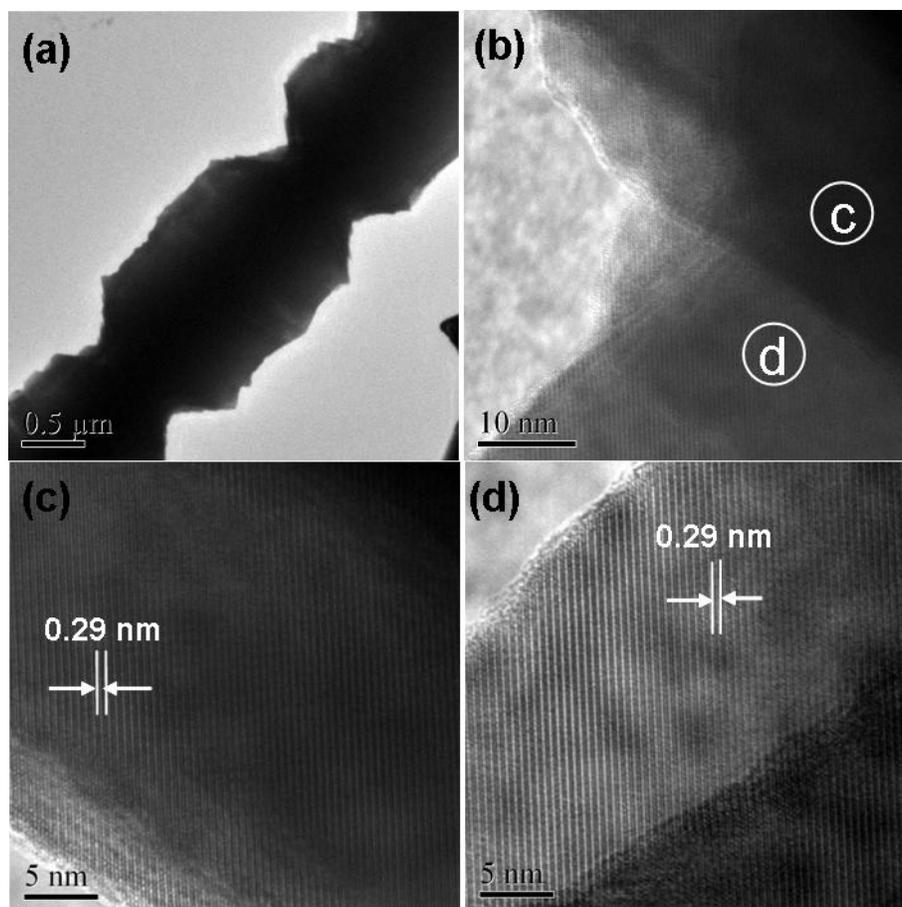


Fig. S3 (a) TEM image of representative In_2O_3 octahedron strings; (b) HRTEM image of individual In_2O_3 octahedron strings, showing the boundary of the upper and lower part; (c, d) HRTEM images of the individual In_2O_3 octahedron strings, exhibiting that both the upper and lower part of the crystals in the In_2O_3 octahedron strings grew in the same direction.

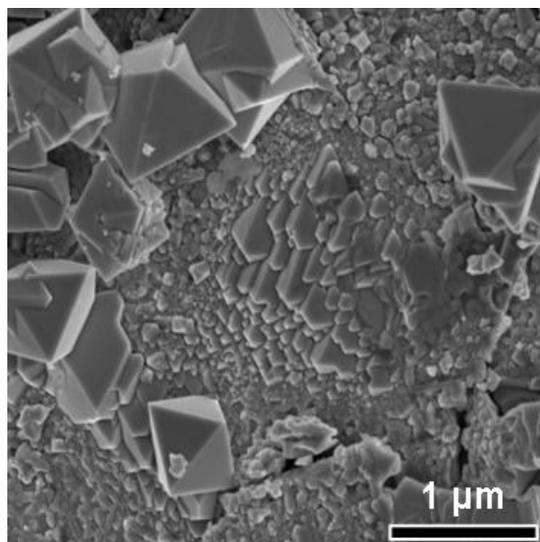


Fig. S4 SEM image of the as-obtained In₂O₃ product (re-introducing air to the evacuated reaction system).

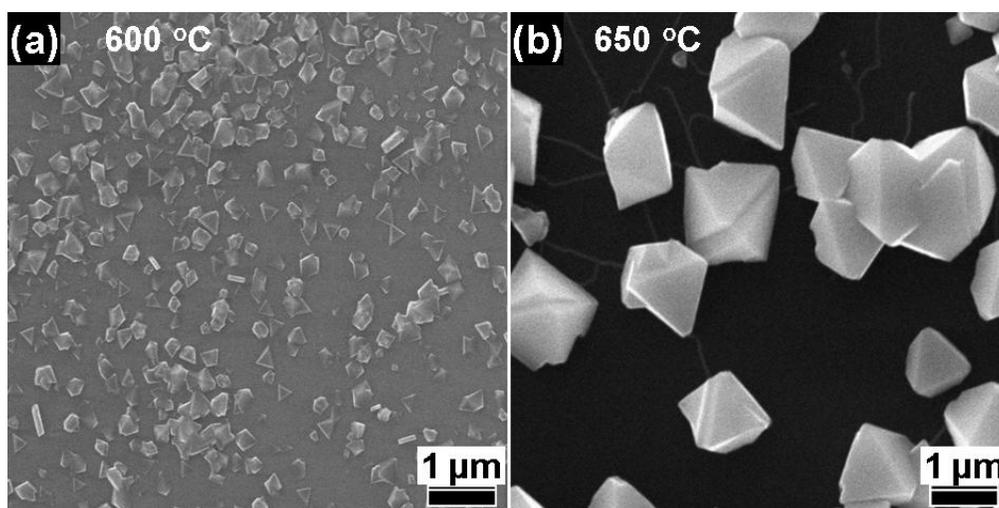


Fig. S5 SEM images of In₂O₃ structures deposited on the surface of the silicon substrates located at region 1 using 100 mg In₂O₃ as starting materials at (a) 600 °C and (b) 650 °C, respectively.

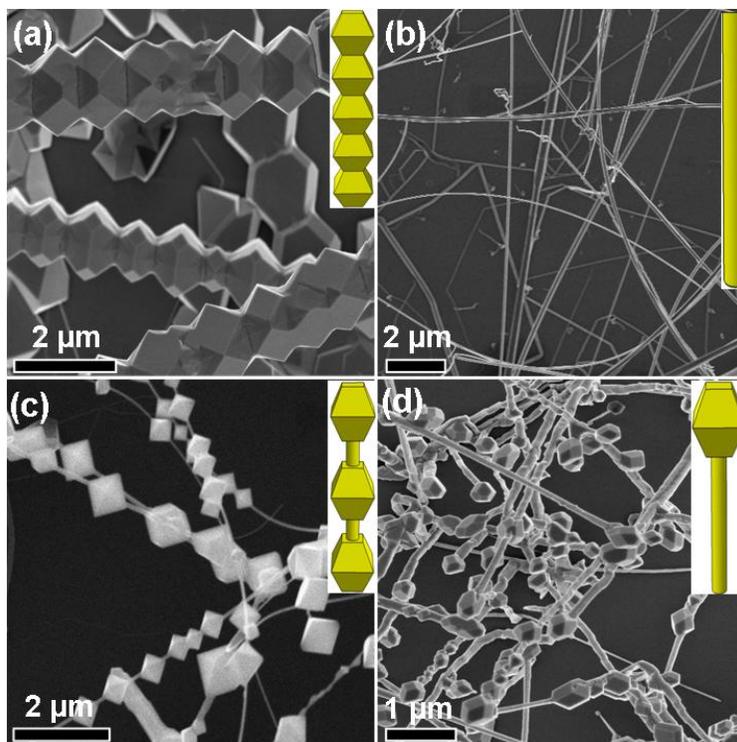


Fig. S6 SEM images of the (a) octahedron strings, (b) nanowires, (c) crystal chains, and (d) lollipop-like structures. All the insets were schematically illustrated in every SEM images.